

#### INTRODUCE:

HVGT high voltage silicon rectifier assembly is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

#### FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

#### APPLICATIONS:

1. High frequency switching power supply.
2. Power supply of laser equipment .
3. General purpose high voltage rectifier.
4. Other.

#### MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 340 grams (approx).

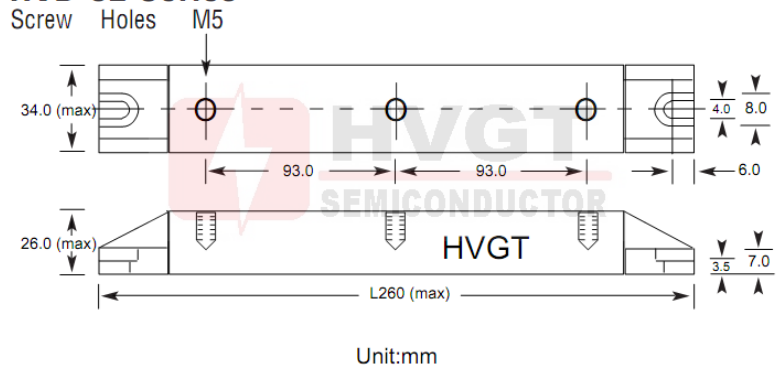
#### SHAPE DISPLAY:



SIZE: (Unit:mm)

HVGT NAME: HVD-32

#### HVD-32 Series



#### MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value		Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_A=25^{\circ}C$	36	36	kV
Average Forward Current Maximum	$I_{FAVM}$	$T_A=25^{\circ}C$	5.0	5.0	A
Suege Current	$I_{FSM}$	$T_A=25^{\circ}C$ ; Half-Sine Wave; 8.3mS	100	100	A
Junction Temperature	$T_J$		125		$^{\circ}C$
Allowable Operation Case Temperature	$T_C$		-40~+125		$^{\circ}C$
Storage Temperature	$T_{STG}$		-40~+125		$^{\circ}C$

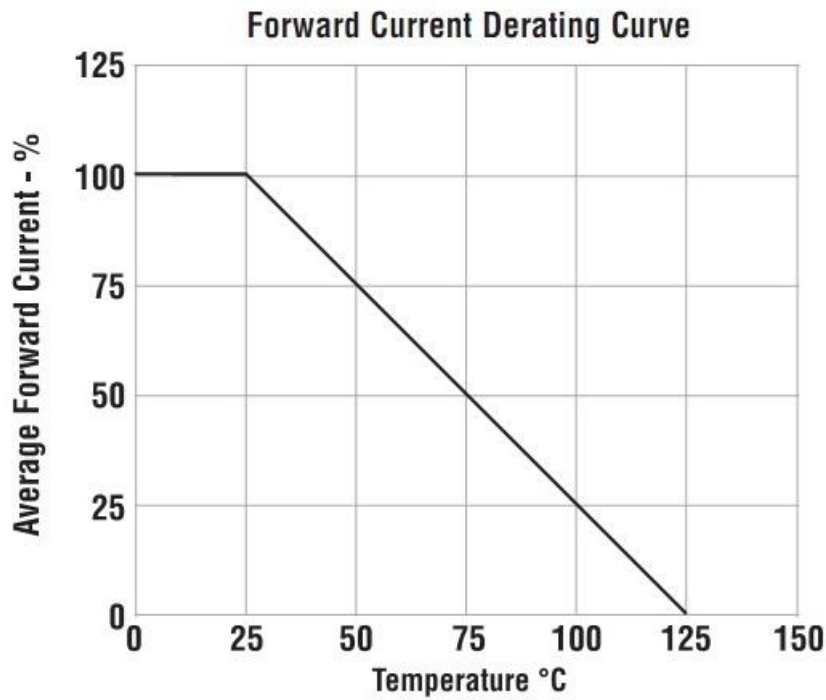
#### ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value		Units
Maximum Forward Voltage Drop	$V_F$	at $25^{\circ}C$ ; at $I_{F(AV)}$	64	64	V
Maximum Reverse Current	$I_{R1}$	at $25^{\circ}C$ ; at $V_{RRM}$	5.0	5.0	$\mu A$
	$I_{R2}$	at $100^{\circ}C$ ; at $V_{RRM}$	50	50	$\mu A$
Maximum Reverse Recovery Time	$T_{RR}$	at $25^{\circ}C$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$	--	--	nS
Junction Capacitance	$C_J$	at $25^{\circ}C$ ; $V_R=0V$ ; $f=1MHz$	--	--	pF



**Fig 1**

**Forward Current Derating Curve**



**Fig 2**

**Non-Repetitive Surge Current**

